

L Number	Hits	Search Text	DB	Time stamp
1	1	("6168991").PN.	USPAT; US-PGPUB	2002/05/03 11:19
-	638	(438/3).CCLS.	USPAT; US-PGPUB	2002/05/02 16:00
-	25944	sputtering and (CVD or "chemical vapor deposition")	USPAT; US-PGPUB	2002/05/02 17:29
-	265	((438/3).CCLS.) and (sputtering and (CVD or "chemical vapor deposition"))	USPAT; US-PGPUB	2002/05/02 16:00
-	1789950	trench or hole or via or opening or recess	USPAT; US-PGPUB	2002/05/02 16:01
-	200	((438/3).CCLS.) and (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess)	USPAT; US-PGPUB	2002/05/02 16:02
-	187	((438/3).CCLS.) and (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and capacitor	USPAT; US-PGPUB	2002/05/02 16:02
-	111	438/387.ccls.	USPAT; US-PGPUB	2002/05/02 16:03
-	13277	ferroelectric or perovskite	USPAT; US-PGPUB	2002/05/02 16:14
-	12	438/387.ccls. and (ferroelectric or perovskite)	USPAT; US-PGPUB	2002/05/02 16:04
-	8	(sputtering and (CVD or "chemical vapor deposition")) and (438/387.ccls. and (ferroelectric or perovskite))	USPAT; US-PGPUB	2002/05/02 16:07
-	22	(sputtering and (CVD or "chemical vapor deposition")) and 438/387.ccls.	USPAT; US-PGPUB	2002/05/02 16:13
-	1325	438/396.ccls.	USPAT; US-PGPUB	2002/05/02 16:14
-	346	(sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls.	USPAT; US-PGPUB	2002/05/02 16:14
-	237950	ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT	USPAT; US-PGPUB	2002/05/02 16:16
-	192	((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls.) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT)	USPAT; US-PGPUB	2002/05/02 16:17
-	176	(trench or hole or via or opening or recess) and (((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls.) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT))	USPAT; US-PGPUB	2002/05/02 16:18
-	172	((trench or hole or via or opening or recess) and (((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls.) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT))) not 438/387.ccls.	USPAT; US-PGPUB	2002/05/02 16:57
-	1283	438/253.ccls.	USPAT; US-PGPUB	2002/05/02 16:58
-	273	(sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.	USPAT; US-PGPUB	2002/05/02 16:58
-	268	capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.)	USPAT; US-PGPUB	2002/05/02 16:59
-	112	(capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.)) not 438/387.ccls. not 438/396.ccls.	USPAT; US-PGPUB	2002/05/02 17:15
-	1350	((lower or bottom) with (electrode or plate)) with sputtering	USPAT; US-PGPUB	2002/05/02 17:18
-	1038	((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition")	USPAT; US-PGPUB	2002/05/02 17:18
-	179	((lower or bottom) with (electrode or plate)) with sputtering and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition"))	USPAT; US-PGPUB	2002/05/02 17:18
-	50679	438/\$.ccls.	USPAT; US-PGPUB	2002/05/02 17:19
-	76	((lower or bottom) with (electrode or plate)) with sputtering and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition")) and 438/\$.ccls.	USPAT; US-PGPUB	2002/05/03 11:19

-	529	438/240.ccls.	USPAT; US-PGPUB	2002/05/02 17:24
-	175	(sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and 438/240.ccls.	USPAT; US-PGPUB	2002/05/02 17:24
-	160	438/244.ccls.	USPAT; US-PGPUB	2002/05/02 17:25
-	9	(sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and 438/244.ccls.	USPAT; US-PGPUB	2002/05/02 17:26
-	17	((((lower or bottom) with (electrode or plate)) with sputtering and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition")))) and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and 438/240.ccls.)	USPAT; US-PGPUB	2002/05/02 17:26
-	316	204/192.17.ccls.	USPAT; US-PGPUB	2002/05/02 17:26
-	1	((((lower or bottom) with (electrode or plate)) with sputtering and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition")))) and 204/192.17.ccls.	USPAT; US-PGPUB	2002/05/02 17:27
-	4	(sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and 204/192.17.ccls.	USPAT; US-PGPUB	2002/05/02 17:28
-	42	438/for.430.ccls.	EPO; JPO; DERWENT	2002/05/02 17:28
-	3804	sputtering and (CVD or "chemical vapor deposition")	EPO; JPO; DERWENT	2002/05/02 17:29
-	0	438/for.430.ccls. and (sputtering and (CVD or "chemical vapor deposition"))	EPO; JPO; DERWENT	2002/05/02 17:29
-	262545	capacitor	EPO; JPO; DERWENT	2002/05/02 17:30
-	32	438/for.430.ccls. and capacitor	EPO; JPO; DERWENT	2002/05/02 17:30
-	57	438/for.220.ccls.	EPO; JPO; DERWENT	2002/05/02 17:30
-	21	capacitor and 438/for.220.ccls.	EPO; JPO; DERWENT	2002/05/02 17:31